DATA SHEET



MOS FIELD EFFECT TRANSISTOR 2SK4078

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

The 2SK4078 is N-channel MOS Field Effect Transistor designed for high current switching applications.

ORDERING INFORMATION

PART NUMBER	LEAD PLATING	PACKING	PACKAGE	
2SK4078-ZK-E1-AY Note	Duna Ca (Tia)	Tono 2500 m/m ol	TO-252 (MP-3ZK)	
2SK4078-ZK-E2-AY Note	Pure Sn (Tin) Tape 2500 p/reel		typ. 0.27 g	

Note Pb-free (This product does not contain Pb in external electrode.)

FEATURES

• Low on-state resistance

 $R_{DS(on)1}$ = 8.5 m Ω MAX. (VGS = 10 V, ID = 25 A) $R_{DS(on)2}$ = 14.0 m Ω MAX. (VGS = 4.5 V, ID = 13 A)

• Low input capacitance

C_{iss} = 2300 pF TYP.

• Logic level drive type

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (V _{GS} = 0 V)	VDSS	40	V
Gate to Source Voltage (VDS = 0 V)	Vgss	±20	V
Drain Current (DC) (Tc = 25°C)	ID(DC)	±50	Α
Drain Current (pulse) Note1	D(pulse)	±150	Α
Total Power Dissipation (Tc = 25°C)	P _{T1}	45	W
Total Power Dissipation (T _A = 25°C)	P _{T2}	1.0	W
Channel Temperature	Tch	150	°С
Storage Temperature	T _{stg}	-55 to +150	°C
Single Avalanche Current Note2	las	23	Α
Single Avalanche Energy Note2	Eas	52	mJ

Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

2. Starting T_{ch} = 25°C, V_{DD} = 20 V, R_G = 25 Ω , V_{GS} = 20 \rightarrow 0 V, L = 100 μ H

THERMAL RESISTANCE

Channel to Case Thermal Resistance	Rth(ch-C)	2.77	°C/W
Channel to Ambient Thermal Resistance	Rth(ch-A)	125	°C/W

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(TO-252)



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ELECTRICAL CHARACTERISTICS (TA = 25°C)

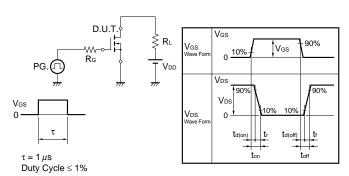
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 40 V, V _{GS} = 0 V			1	μА
Gate Leakage Current	Igss	V _{GS} = ±20 V, V _{DS} = 0 V			±100	nA
Gate to Source Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	1.5	2.0	2.5	V
Forward Transfer Admittance Note	yfs	V _{DS} = 10 V, I _D = 25 A	7.0			S
Drain to Source On-state Resistance Note	RDS(on)1	V _{GS} = 10 V, I _D = 25 A		6.3	8.5	mΩ
	RDS(on)2	V _{GS} = 4.5 V, I _D = 13 A		9.5	14.0	mΩ
Input Capacitance	Ciss	V _{DS} = 10 V,		2300		pF
Output Capacitance	Coss	V _{GS} = 0 V,		360		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		220		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 20 V, I _D = 25 A,		12		ns
Rise Time	tr	V _{GS} = 10 V,		15		ns
Turn-off Delay Time	td(off)	R _G = 0 Ω		51		ns
Fall Time	tr			9		ns
Total Gate Charge	Q _G	V _{DD} = 32 V,		45		nC
Gate to Source Charge	Qgs	V _{GS} = 10 V,		7		nC
Gate to Drain Charge	Q _{GD}	I _D = 50 A		13		nC
Body Diode Forward Voltage Note	V _{F(S-D)}	I _F = 50 A, V _{GS} = 0 V			1.5	V
Reverse Recovery Time	trr	I _F = 50 A, V _{GS} = 0 V,		30		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		26		nC

Note Pulsed

TEST CIRCUIT 1 AVALANCHE CAPABILITY

$V_{GS} = 20 \rightarrow 0 \text{ V}$ V_{DS} V_{DS} V_{DS} V_{DS} V_{DS} V_{DS} V_{DS} V_{DS} V_{DS} V_{DS}

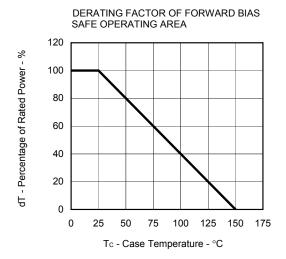
TEST CIRCUIT 2 SWITCHING TIME

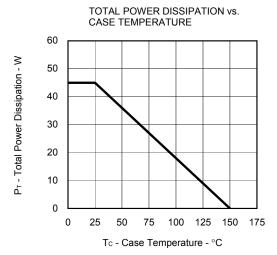


TEST CIRCUIT 3 GATE CHARGE

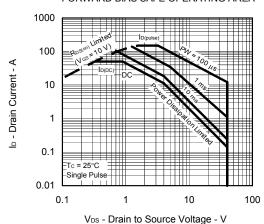
$$\begin{array}{c|c} D.U.T. \\ \hline \\ lg = 2 \text{ mA} \\ \hline \\ VOD \\ \end{array}$$

TYPICAL CHARACTERISTICS (TA = 25°C)

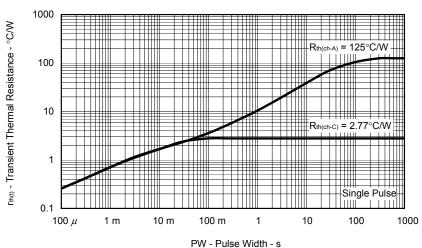




FORWARD BIAS SAFE OPERATING AREA

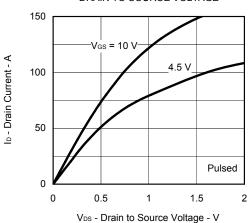


TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

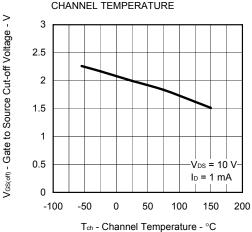


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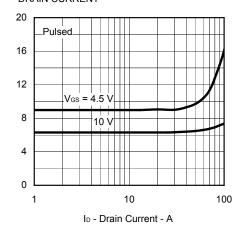
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



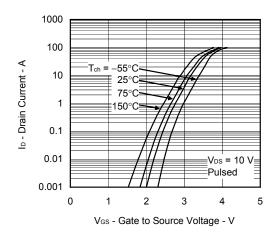
GATE TO SOURCE CUT-OFF VOLTAGE vs.



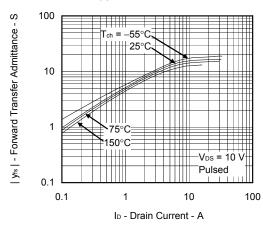
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



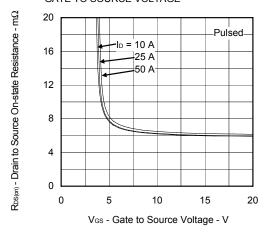
FORWARD TRANSFER CHARACTERISTICS



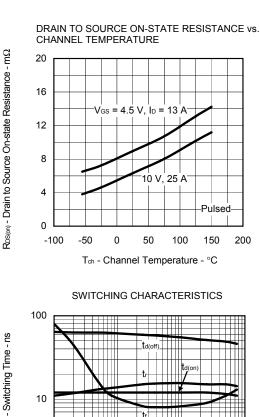
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

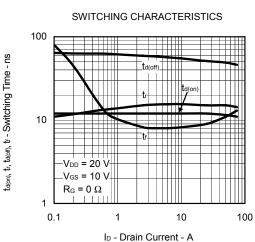


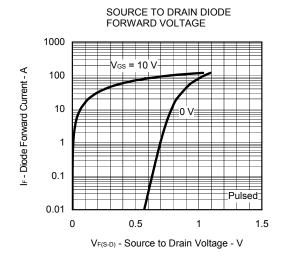
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



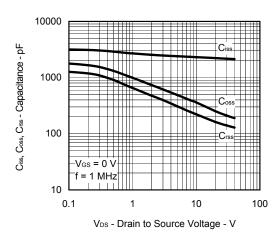
R_{DS(m)} - Drain to Source On-state Resistance - mΩ



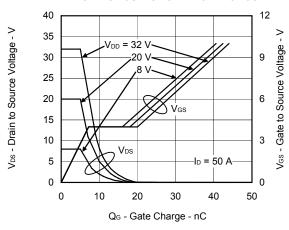




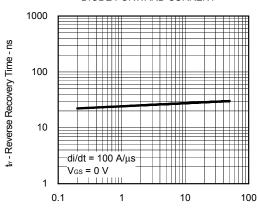




DYNAMIC INPUT/OUTPUT CHARACTERISTICS



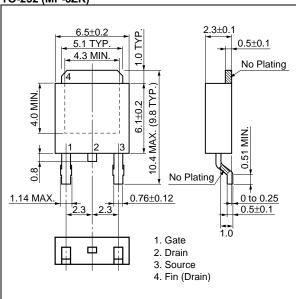
REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



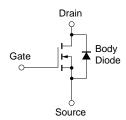
IF - Diode Forward Current - A

PACKAGE DRAWING (Unit: mm)





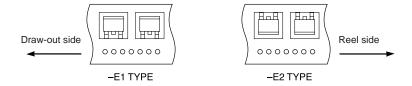
EQUIVALENT CIRCUIT



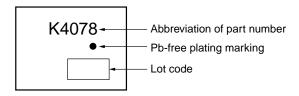
Remark Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

TAPE INFORMATION

There are two types (-E1, -E2) of taping depending on the direction of the device.



MARKING INFORMATION



RECOMMENDED SOLDERING CONDITIONS

The 2SK4078 should be soldered and mounted under the following recommended conditions.

For soldering methods and conditions other than those recommended below, please contact an NEC Electronics sales representative.

For technical information, see the following website.

Semiconductor Device Mount Manual (http://www.necel.com/pkg/en/mount/index.html)

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared reflow	Maximum temperature (Package's surface temperature): 260°C or below	IR60-00-3
	Time at maximum temperature: 10 seconds or less	
	Time of temperature higher than 220°C: 60 seconds or less	
	Preheating time at 160 to 180°C: 60 to 120 seconds	
	Maximum number of reflow processes: 3 times	
	Maximum chlorine content of rosin flux (percentage mass): 0.2% or less	
Partial heating	Maximum temperature (Pin temperature): 350°C or below	P350
	Time (per side of the device): 3 seconds or less	
	Maximum chlorine content of rosin flux: 0.2% (wt.) or less	

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